Silicon PNP Power Transistors 2SA808

DESCRIPTION

·With TO-3 package
·Wide area of safe operation
·Complement to type 2SC1619

APPLICATIONS

·For power amplifier and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-6	A
I_B	Base current		-3	A
P_C	Collector power dissipation	T_C=25□	50	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-65~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-50mA I_B=0	-80			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-3A; I_B=-0.3A			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-80V; I_E=0			-1.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-6V; I_C=0			-1.0	mA
h_{FE}	DC current gain	I_C=-3A ; V_{CE}=-4V	20			
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=-12V		10		MHz
Switching times						
t_r	Rise time	V_{CC}=-10V;I_C=-3A; R_L=3Ω I_{B1}=-0.3A; I_{B2}=50mA		1.2		μs
t_{stg}	Storage time			1.8		μs
t_f	Fall time			0.3		μs

PACKAGE OUTLINE

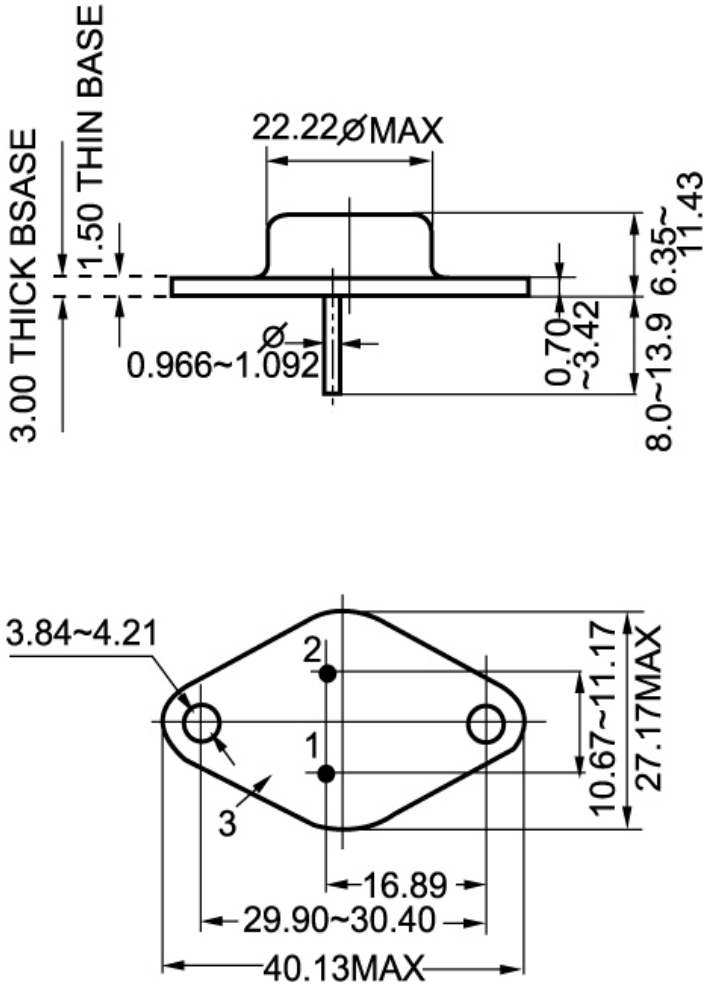

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)